

High Efficiency Thyristor

$$V_{RRM} = 1200\text{ V}$$

$$I_{TAV} = 50\text{ A}$$

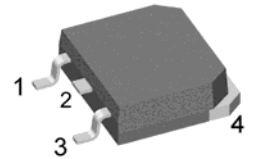
$$V_T = 1,27\text{ V}$$

Single Thyristor

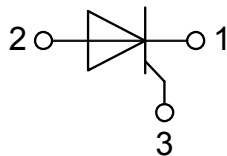
Part number

CLA50E1200TC

Marking on Product: CLA50E1200TC



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-268AA (D3Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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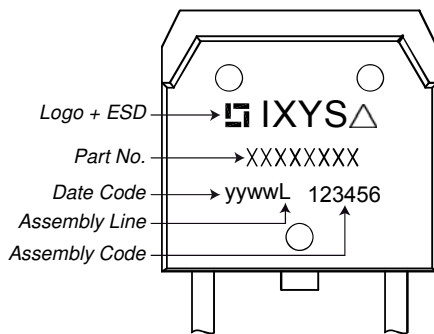


Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_{RD}	reverse current, drain current	$V_{RD} = 1200 V$	$T_{VJ} = 25^{\circ}C$		50	μA
		$V_{RD} = 1200 V$	$T_{VJ} = 125^{\circ}C$		4	mA
V_T	forward voltage drop	$I_T = 50 A$	$T_{VJ} = 25^{\circ}C$		1,32	V
		$I_T = 100 A$			1,60	V
		$I_T = 50 A$	$T_{VJ} = 125^{\circ}C$		1,27	V
		$I_T = 100 A$			1,65	V
I_{TAV}	average forward current	$T_C = 125^{\circ}C$	$T_{VJ} = 150^{\circ}C$		50	A
$I_{T(RMS)}$	RMS forward current	180° sine			79	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0,88	V
r_T	slope resistance				7,7	m Ω
R_{thJC}	thermal resistance junction to case				0,25	K/W
R_{thCH}	thermal resistance case to heatsink			0,15		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		500	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		650	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		700	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		555	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		595	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		2,12	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		2,04	kA ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		1,54	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1,48	kA ² s
C_J	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		25	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 150 A$		150	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0,3 A/\mu s;$ $I_G = 0,3 A; V_D = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 50 A$		500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 150^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1,5	V
			$T_{VJ} = -40^{\circ}C$		1,6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		50	mA
			$T_{VJ} = -40^{\circ}C$		80	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0,2	V
I_{GD}	gate non-trigger current				3	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		125	mA
		$I_G = 0,3 A; di_G/dt = 0,3 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0,3 A; di_G/dt = 0,3 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 50 A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		200	μs



Package TO-268AA (D3Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				5		g
F_c	mounting force with clip		20		120	N

Product Marking



Part description

- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 50 = Current Rating [A]
- E = Single Thyristor
- 1200 = Reverse Voltage [V]
- TC = TO-268AA (D3Pak) (2)

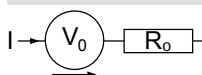
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA50E1200TC-TUB	CLA50E1200TC	Tube	30	502708
Alternative	CLA50E1200TC-TRL	CLA50E1200TC	Tape & Reel	400	502737

Similar Part	Package	Voltage class
CLA50E1200HB	TO-247AD (3)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Thyristor

$V_{0\ max}$	threshold voltage	0,88	V
$R_{0\ max}$	slope resistance *	5,2	mΩ

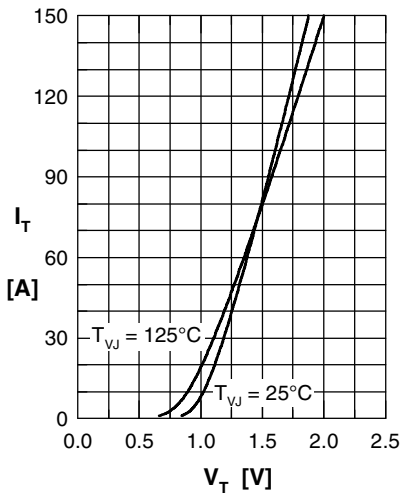
Thyristor


Fig. 1 Forward characteristics

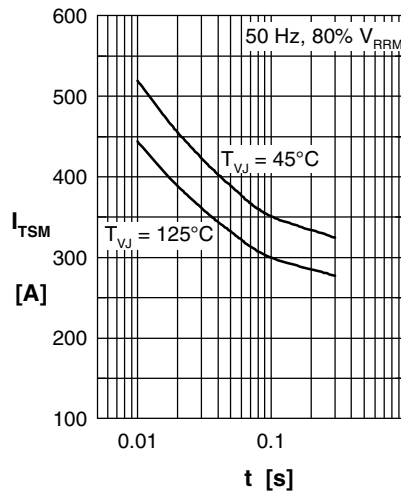
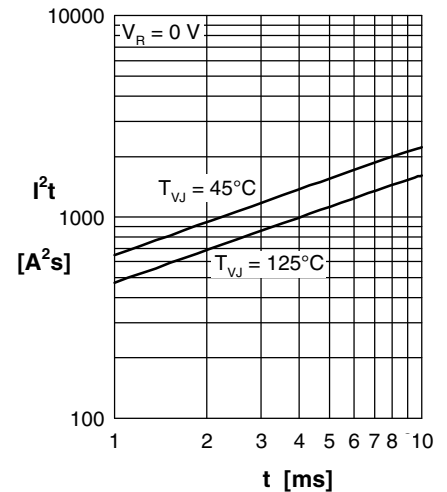
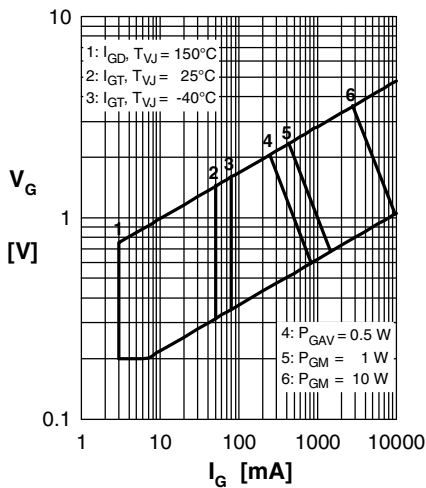

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

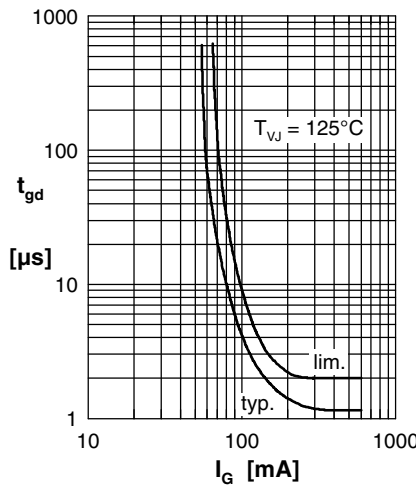
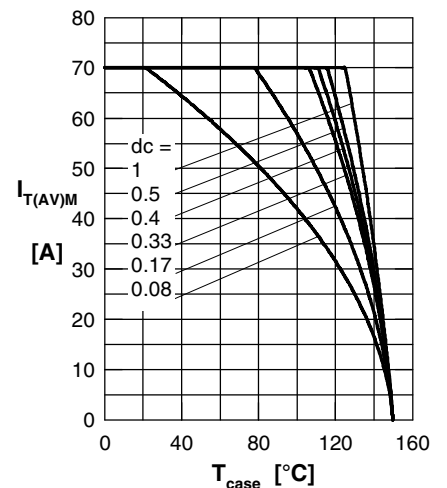

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

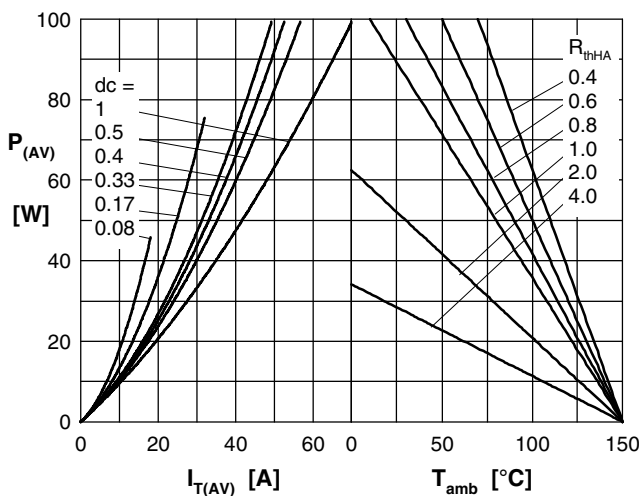
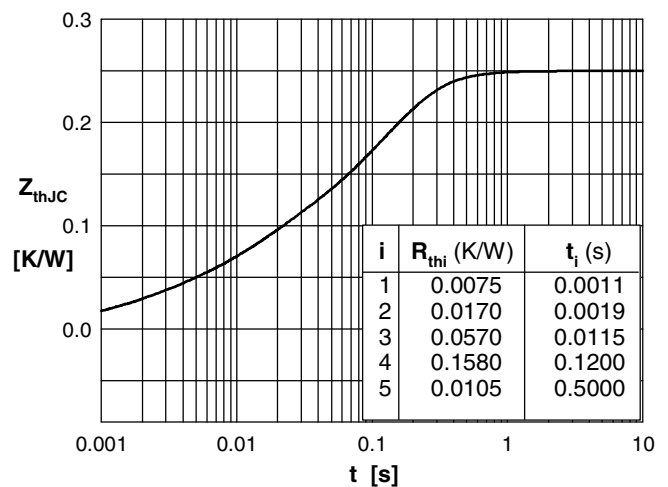

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 7 Transient thermal impedance junction to case